

## KSP92/93

## **High Voltage Transistor**



# PNP Epitaxial Silicon Transistor

### **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	7 124 124	
	: KSP92	-300	V
	: KSP93	-200	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	: KSP92	-300	V
	: KSP93	-200	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
Ic	Collector Current	-500	mA
Pc	Collector Power Dissipation (T <sub>a</sub> =25°C)	625	mW
	Derate above 25°C	5	mW/°C
P <sub>C</sub>	Collector Power Dissipation (T <sub>C</sub> =25°C)	1.5	W
	Derate above 25°C	12	mW/°C
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage : KSP92 : KSP93	I <sub>C</sub> = -100μA, I <sub>E</sub> =0	-300 -200		V V
BV <sub>CEO</sub>	* Collector-Emitter Breakdown Voltage : KSP92 : KSP93	I <sub>C</sub> = -1mA, I <sub>B</sub> =0	-300 -200	市	V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -100μA, I <sub>C</sub> =0	-5	4.07	V
I <sub>CBO</sub>	Collector Cur-off Current : KSP92 : KSP93	V <sub>CB</sub> = -200V, I <sub>E</sub> =0 V <sub>CB</sub> = -160V, I <sub>E</sub> =0	MAG	-0.25 -0.25	μA μA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = -3V, I <sub>C</sub> =0		-0.10	μΑ
h <sub>FE</sub>	* DC Current Gain	$V_{CE}$ = -10V, $I_{CE}$ = -1mA $V_{CE}$ = -10V, $I_{CE}$ = -10mA $V_{CE}$ = -10V, $I_{CE}$ = -30mA	25 40 25		
V <sub>CE</sub> (sat)	*Collector-Emitter Saturation Voltage	I <sub>C</sub> = -20mA, I <sub>B</sub> = -2mA		-0.50	V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	I <sub>C</sub> = -20mA, I <sub>B</sub> = -2mA		-0.90	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -20V, I <sub>C</sub> = -10mA, f=100MHz	50		MHz
C <sub>ob</sub>	Output Capacitance : KSP92 : KSP93	V <sub>CB</sub> = -20V, I <sub>E</sub> =0 f=1MHz		6 8	pF pF

\* Pulse Test: PW≤300μs, Duty Cycle≤2%

# **Typical Characteristics**

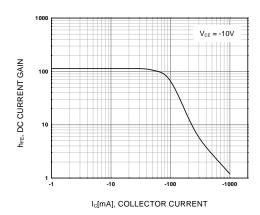


Figure 1. DC current Gain

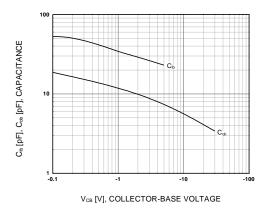


Figure 3. Capacitance

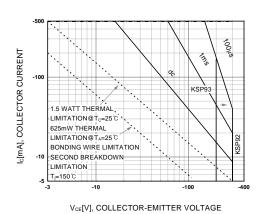


Figure 5. Active-Regio Safe Operating Area

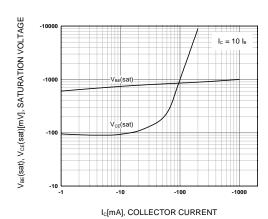


Figure 2. Saturation Voltage

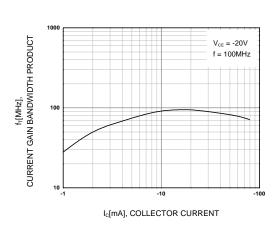
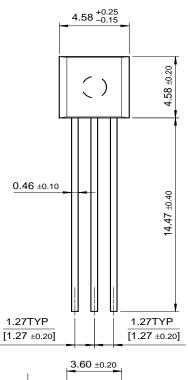


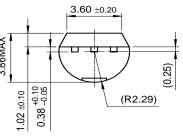
Figure 4. Current Gain Bandwidth Product

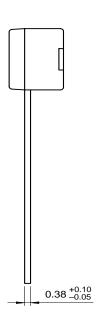
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# **Package Demensions**

TO-92







Dimensions in Millimeters

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